



IXFX100N65X2 Information



For Reference Only

Part Number IXFX100N65X2

Manufacturer IXYS

Category Discrete Semiconductor Products

Transistors - FETs, MOSFETs - Single

Description MOSFET N-CH 650V 100A PLUS247

Package TO-247-3

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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IXFX100N65X2 Specifications

Manufacturer Part Number IXFX100N65X2 Manufacturer IXYS Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package TO-247-3 Series HiPerFET? FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 650V Current - Continuous Drain (Id) @ 25°C 100A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 5.5V @ 4mA Gate Charge (Qg) (Max) @ Vgs 180nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 1300pF @ 25V Vgs (Max) ±300P @ 25V Vgs (Max) ±300P @ 25V Vgs (Max) 1040W (Tc) Rds On (Max) @ Id, Vgs 30 mOhm @ 50A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package PLUS247?-3 Package / Case TO-247-3 Report errors?		
Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single TO-247-3 Series HiPerFET? FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature John (Max) @ Id, Vgs Mounting Type Through Hole Supplier Device Package PLUS247-3 Package / Case	Manufacturer Part Number	IXFX100N65X2
Package TO-247-3 Series HiPerFET? FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 650V Current - Continuous Drain (Id) @ 25°C 100A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 5.5V @ 4mA Gate Charge (Qg) (Max) @ Vgs 180nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 11300pF @ 25V Vgs (Max) ±30V FET Feature - Power Dissipation (Max) 1040W (Tc) Rds On (Max) @ Id, Vgs 30 mOhm @ 50A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package PLUS247?-3 Package / Case TO-247-3	Manufacturer	IXYS
Package TO-247-3 Series HiPerFET? FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 650V Current - Continuous Drain (Id) @ 25°C 100A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 5.5V @ 4mA Gate Charge (Qg) (Max) @ Vgs 180nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 11300pF @ 25V Vgs (Max) ±30V FET Feature - Power Dissipation (Max) 1040W (Tc) Rds On (Max) @ Id, Vgs 30 mOhm @ 50A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package PLUS247?-3 Package / Case TO-247-3	Category	Discrete Semiconductor Products
SeriesHiPerFET?FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)650VCurrent - Continuous Drain (Id) @ 25°C100A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id5.5V @ 4mAGate Charge (Qg) (Max) @ Vgs180nC @ 10VInput Capacitance (Ciss) (Max) @ Vds11300pF @ 25VVgs (Max)±30VFET Feature-Power Dissipation (Max)1040W (Tc)Rds On (Max) @ Id, Vgs30 mOhm @ 50A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackagePLUS247?-3Package / CaseTO-247-3		Transistors - FETs, MOSFETs - Single
FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C 100A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 5.5V @ 4mA Gate Charge (Qg) (Max) @ Vgs 180nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 11300pF @ 25V Vgs (Max) ±30V FET Feature - Power Dissipation (Max) 1040W (Tc) Rds On (Max) @ Id, Vgs 30 mOhm @ 50A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package PLUS247?-3 Package / Case Took Carrent Source (Max) MOSFET (Metal Oxide) MOSFET (Metal Oxide) MOSFET (Metal Oxide) 1040W (Tc) 1150PC (TJ) 1150PC (TJ	Package	TO-247-3
Technology Drain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature Supplier Device Package PLUS247?-3 Package / Case MOSFET (Metal Oxide) MOSFET (Metal Oxide) 650V MOSFET (Metal Oxide) 650V 650V 100A (Tc) 1040 (Tc) 1180nC @ 10V 11300pF @ 25V 25V 25V 25V 25V 25V 25V 25V	Series	HiPerFET?
Drain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id S.5V @ 4mA Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature Supplier Device Package Package / Case 100A (Tc) 100	FET Type	N-Channel
Current - Continuous Drain (Id) @ 25°C Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id 5.5V @ 4mA Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 30 mOhm @ 50A, 10V Operating Temperature Supplier Device Package PLUS247?-3 Package / Case 100A (Tc) 100	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id 5.5V @ 4mA Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 30 mOhm @ 50A, 10V Operating Temperature Supplier Device Package PLUS247?-3 Package / Case 10V 180n @ 4mA 180n @ 10V 11300pF @ 25V 11300pF @ 25V	Drain to Source Voltage (Vdss)	650V
Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature Supplier Device Package Pulys247?-3 Package / Case 180nC @ 10V 11300pF @ 25V ±30V +30V 1040W (Tc) 30 mOhm @ 50A, 10V -55°C ~ 150°C (TJ) Through Hole PLUS247?-3 Package / Case TO-247-3	Current - Continuous Drain (Id) @ 25°C	100A (Tc)
Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds 11300pF @ 25V Vgs (Max) ET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature John C @ 10V 1040W (Tc) 30 mOhm @ 50A, 10V Operating Temperature John C TJ Through Hole Supplier Device Package PLUS247?-3 Package / Case TO-247-3	Drive Voltage (Max Rds On, Min Rds On)	10V
Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) ET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package Package / Case TO-247-3	Vgs(th) (Max) @ Id	5.5V @ 4mA
Vgs (Max)±30VFET Feature-Power Dissipation (Max)1040W (Tc)Rds On (Max) @ Id, Vgs30 mOhm @ 50A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackagePLUS247?-3Package / CaseTO-247-3	Gate Charge (Qg) (Max) @ Vgs	180nC @ 10V
FET Feature - 1040W (Tc) Rds On (Max) @ Id, Vgs 30 mOhm @ 50A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package PLUS247?-3 Package / Case TO-247-3	Input Capacitance (Ciss) (Max) @ Vds	11300pF @ 25V
Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package Package / Case TO-247-3	Vgs (Max)	±30V
Rds On (Max) @ Id, Vgs30 mOhm @ 50A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackagePLUS247?-3Package / CaseTO-247-3	FET Feature	-
Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package PLUS247?-3 Package / Case TO-247-3	Power Dissipation (Max)	1040W (Tc)
Mounting Type Through Hole Supplier Device Package PLUS247?-3 Package / Case TO-247-3	Rds On (Max) @ Id, Vgs	30 mOhm @ 50A, 10V
Supplier Device Package PLUS247?-3 Package / Case TO-247-3	Operating Temperature	-55°C ~ 150°C (TJ)
Package / Case TO-247-3	Mounting Type	Through Hole
	Supplier Device Package	PLUS247?-3
Report errors?	Package / Case	TO-247-3
		Report errors?

IXFX100N65X2 Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

IXFX100N65X2 Payment Methods



















IXFX100N65X2 Shipping Methods













If you have any question about IXFX100N65X2, please do not hesitate to contact us!

Website: https://www.heisener.com E-mail: salesdept@heisener.com